# DSC2501

### Silicon NPN epitaxial planar type

#### For low frequency amplification

#### Features

- Low collector-emitter saturation voltage  $V_{CE(sat)}$
- Contributes to miniaturization of sets, reduction of component count.
- Eco-friendly Halogen-free package

#### Packaging

Embossed type (Thermo-compression sealing): 3000 pcs / reel (standard)

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	25	V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	20	V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	12	V
Collector current	I <sub>C</sub>	0.5	А
Peak collector current	I <sub>CP</sub>	1	А
Collector power dissipation	P <sub>C</sub>	200	mW
Junction temperature	Tj	150	°C
Storage temperature	T <sub>stg</sub>	-55 to +150	°C

#### Package

- Code
- Mini3-G3-B-B
- Pin Name
  - 1. Base
  - 2. Emitter
  - 3. Collector

#### Marking Symbol: E3

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu {\rm A}, I_{\rm E} = 0$	25			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	20			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu {\rm A}, I_{\rm C} = 0$	12			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 25 \text{ V}, I_E = 0$			100	nA
Forward current transfer ratio *2	h <sub>FE</sub>	$V_{CE} = 2 V, I_C = 0.5 A$	200		800	
Collector-emitter saturation voltage *1	V <sub>CE(sat)</sub>	$I_{\rm C} = 0.5  \text{A}, I_{\rm B} = 20  \text{mA}$		0.18	0.40	V
Base-emitter saturation voltage *1	V <sub>BE(sat)</sub>	$I_{\rm C} = 0.5  \text{A}, I_{\rm B} = 50  \text{mA}$			1.2	V
Transition frequency	f <sub>T</sub>	$V_{CE} = 10 \text{ V}, I_C = 50 \text{ mA}$		150		MHz
Collector output capacitance (Common base, input open circuited)	C <sub>ob</sub>	$V_{CB} = 10 \text{ V}, I_E = 0, f = 1 \text{ MHz}$		6		pF
ON resistance *3	R <sub>on</sub>			1.0		Ω

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

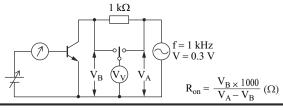
2. \*1: Pulse measurement

*2:	Rank	classification	

Code	R	S	Т	0
Rank	R	S	Т	No-rank
h <sub>FE</sub>	200 to 350	300 to 500	400 to 800	200 to 800
Marking Symbol	E3R	E3S	E3T	E3

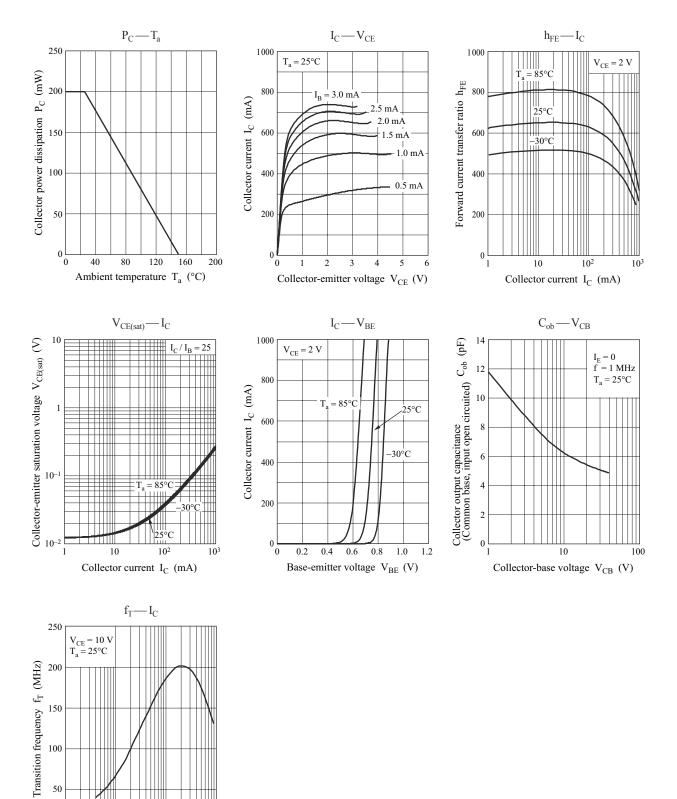
Product of no-rank is not classified and have no marking symbol for rank.

\*3: Ron measurement circuit



#### DSC2501

### **Panasonic**



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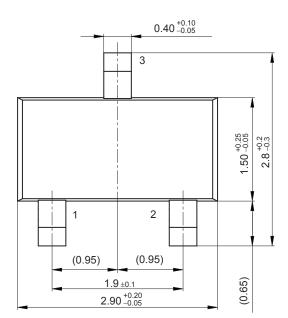
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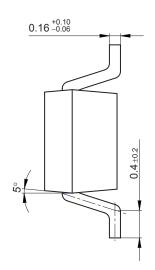
Collector current I<sub>C</sub> (mA)

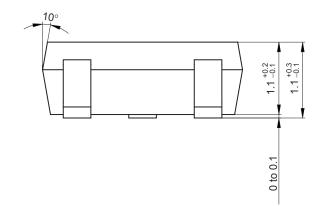
100

### Mini3-G3-B-B

Unit: mm







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